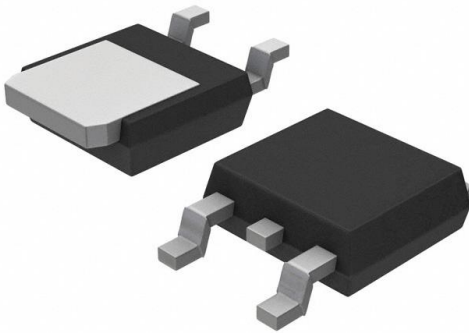


MJD2955T4G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	MJD2955T4G-DG
Manufacturer	onsemi
Manufacturer Product Number	MJD2955T4G
Description	TRANS PNP 60V 10A DPAK
Detailed Description	Bipolar (BJT) Transistor PNP 60 V 10 A 2MHz 1.75 W Surface Mount DPAK



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

MJD2955T4G

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

60 V

Current - Collector Cutoff (Max):

50 μ A

Power - Max:

1.75 W

Operating Temperature:

-55°C ~ 150°C (TJ)

Package / Case:

TO-252-3, DPAK (2 Leads + Tab), SC-63

Base Product Number:

MJD2955

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

10 A

Vce Saturation (Max) @ Ib, Ic:

8V @ 3.3A, 10A

DC Current Gain (hFE) (Min) @ Ic, Vce:

20 @ 4A, 4V

Frequency - Transition:

2MHz

Mounting Type:

Surface Mount

Supplier Device Package:

DPAK

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MJD2955 (PNP), MJD3055 (NPN)

Complementary Power Transistors

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“-1” Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain–Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V_{CEO}	60	Vdc
Collector–Base Voltage	V_{CB}	70	Vdc
Emitter–Base Voltage	V_{EB}	5	Vdc
Collector Current	I_C	10	Adc
Base Current	I_B	6	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D^\dagger	20 0.16	W W/ $^\circ\text{C}$
Total Power Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.75 0.014	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	C	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

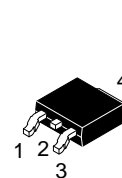
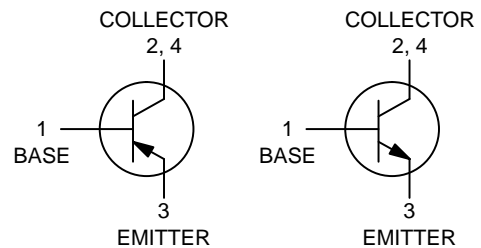


ON Semiconductor®

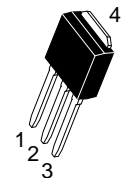
<http://onsemi.com>

SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

COMPLEMENTARY

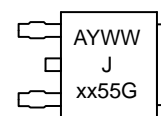


**DPAK
CASE 369C
STYLE 1**

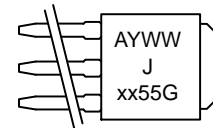


**IPAK
CASE 369D
STYLE 1**

MARKING DIAGRAMS



DPAK



IPAK

- A = Assembly Location
- Y = Year
- WW = Work Week
- Jxx55 = Device Code
x = 29 or 30
- G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MJD2955 (PNP), MJD3055 (NPN)**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	71.4	$^{\circ}\text{C}/\text{W}$

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 3) ($I_C = 30 \text{ mAdc}$, $I_B = 0$)	$V_{CE(sus)}$	60	–	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	–	50	μAdc
Collector Cutoff Current ($V_{CE} = 70 \text{ Vdc}$, $V_{EB(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 70 \text{ Vdc}$, $V_{EB(off)} = 1.5 \text{ Vdc}$, $T_C = 150^{\circ}\text{C}$)	I_{CEX}	–	$\frac{0.02}{2}$	mAdc
Collector Cutoff Current ($V_{CB} = 70 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 70 \text{ Vdc}$, $I_E = 0$, $T_C = 150^{\circ}\text{C}$)	I_{CBO}	–	$\frac{0.02}{2}$	mAdc
Emitter Cutoff Current ($V_{BE} = 5 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	0.5	mAdc

ON CHARACTERISTICS

DC Current Gain (Note 3) ($I_C = 4 \text{ Adc}$, $V_{CE} = 4 \text{ Vdc}$) ($I_C = 10 \text{ Adc}$, $V_{CE} = 4 \text{ Vdc}$)	h_{FE}	$\frac{20}{5}$	$\frac{100}{-}$	–
Collector-Emitter Saturation Voltage (Note 3) ($I_C = 4 \text{ Adc}$, $I_B = 0.4 \text{ Adc}$) ($I_C = 10 \text{ Adc}$, $I_B = 3.3 \text{ Adc}$)	$V_{CE(sat)}$	–	$\frac{1.1}{8}$	Vdc
Base-Emitter On Voltage (Note 3) ($I_C = 4 \text{ Adc}$, $V_{CE} = 4 \text{ Vdc}$)	$V_{BE(on)}$	–	1.8	Vdc

DYNAMIC CHARACTERISTICS

Current-Gain – Bandwidth Product ($I_C = 500 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 500 \text{ kHz}$)	f_T	2	–	MHz
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3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

MJD2955 (PNP), MJD3055 (NPN)

TYPICAL CHARACTERISTICS

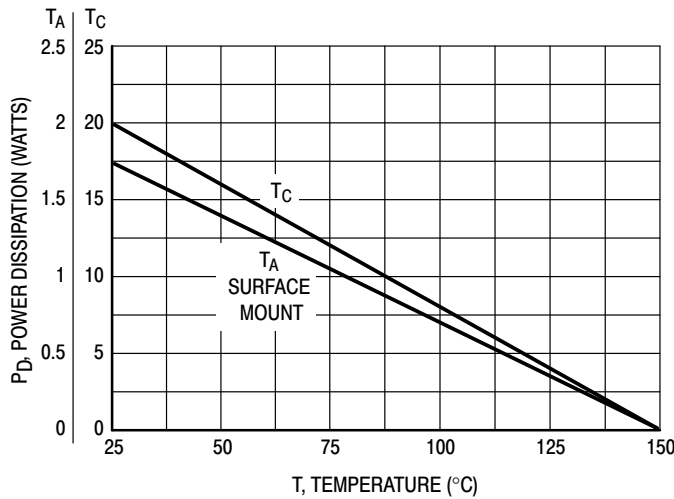


Figure 1. Power Derating

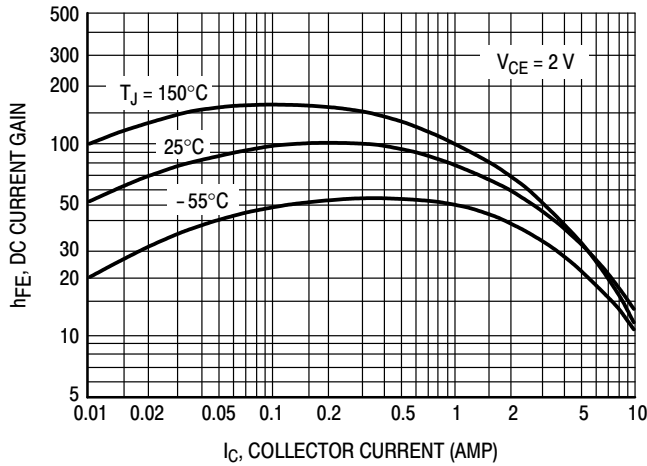


Figure 2. DC Current Gain

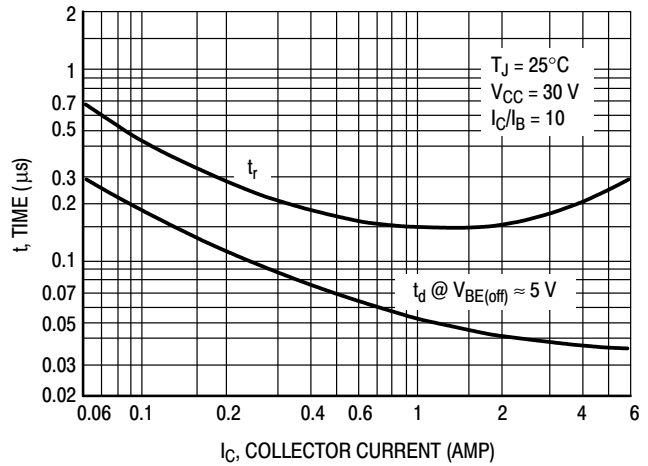


Figure 3. Turn-On Time

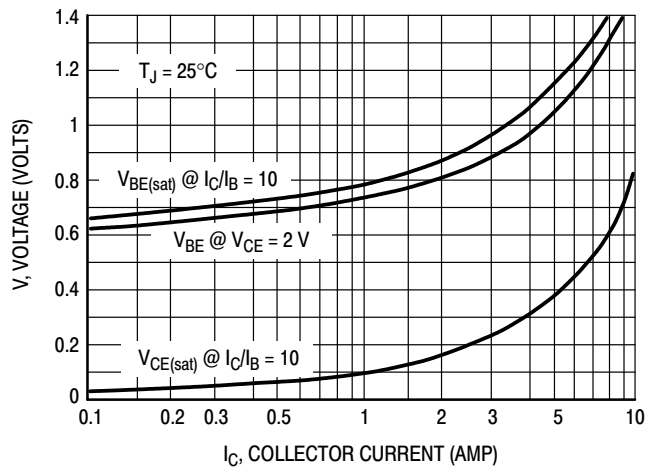


Figure 4. "On" Voltages, MJD3055

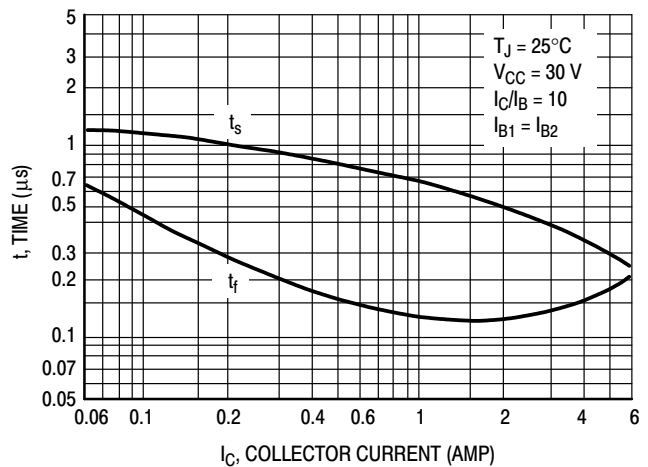


Figure 5. Turn-Off Time

MJD2955 (PNP), MJD3055 (NPN)

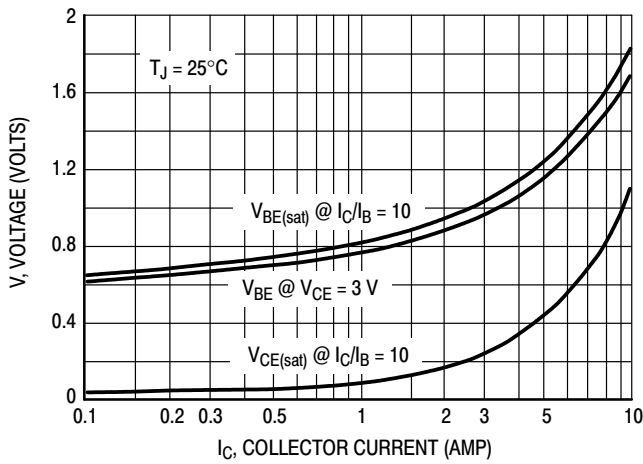


Figure 6. "On" Voltages, MJD2955

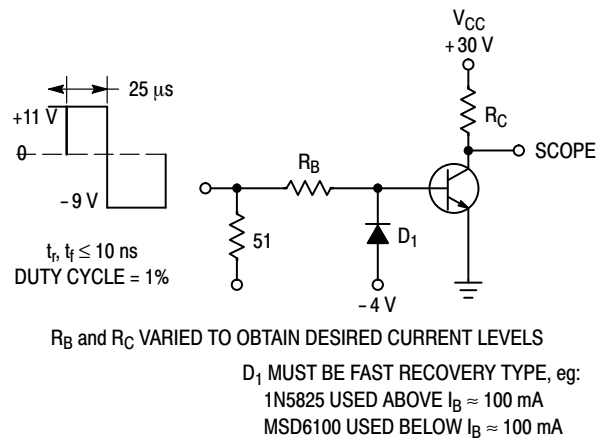


Figure 7. Switching Time Test Circuit

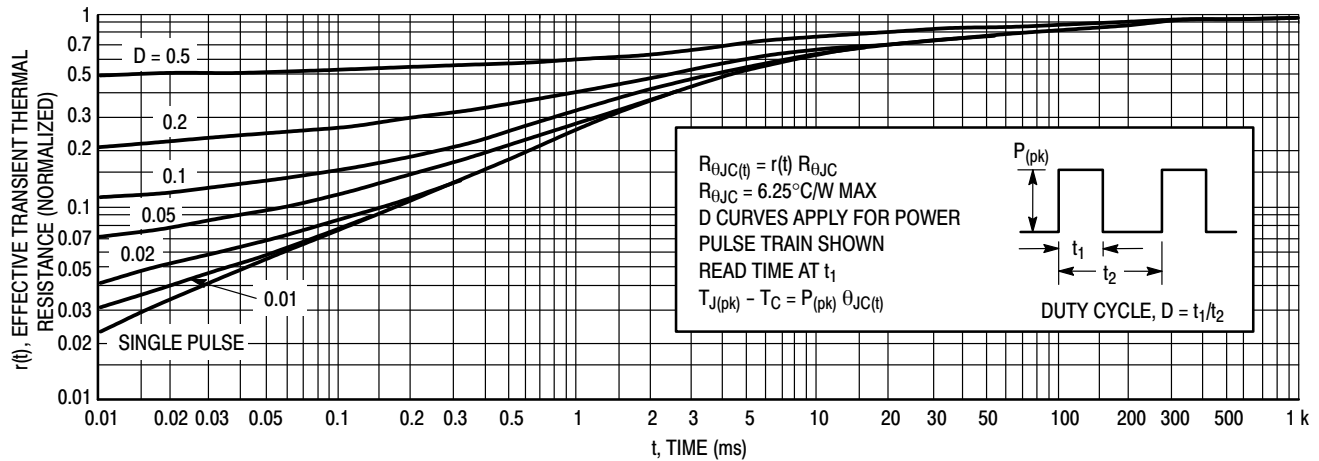


Figure 8. Thermal Response

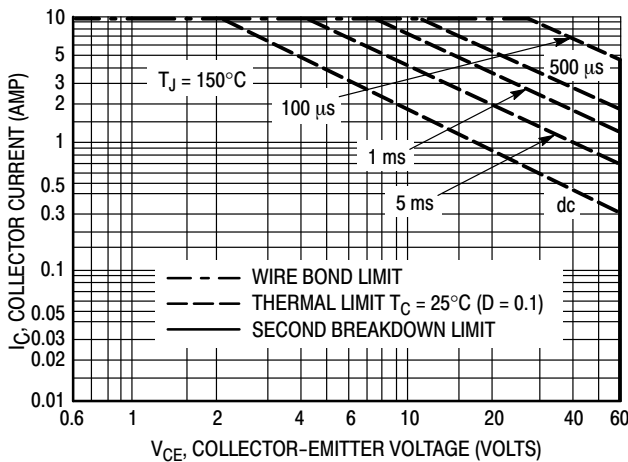


Figure 9. Maximum Forward Bias Safe Operating Area

Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJD2955 (PNP), MJD3055 (NPN)**ORDERING INFORMATION**

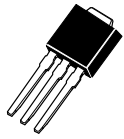
Device	Package Type	Package	Shipping [†]
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable



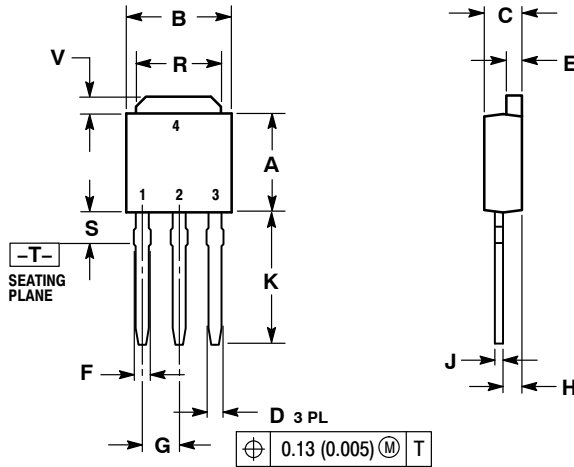
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



**DPAK INSERTION MOUNT
CASE 369
ISSUE O**

DATE 02 JAN 2000

SCALE 1:1



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

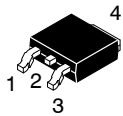
- | | | | | | |
|--|---|---|--|--|--|
| <p>STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR</p> | <p>STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN</p> | <p>STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE</p> | <p>STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE</p> | <p>STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE</p> | <p>STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2</p> |
|--|---|---|--|--|--|

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DESCRIPTION:	DPAK INSERTION MOUNT	PAGE 1 OF 1

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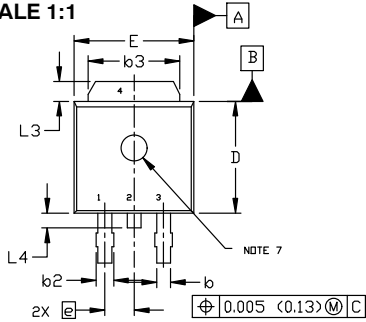
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



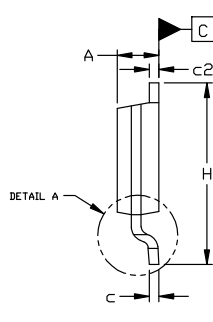
**DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G**

DATE 31 MAY 2023

SCALE 1:1



TOP VIEW

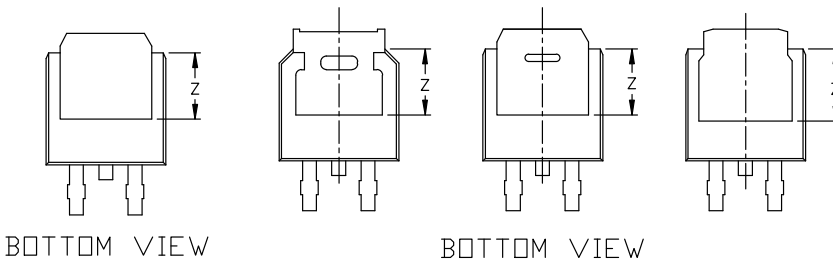


SIDE VIEW

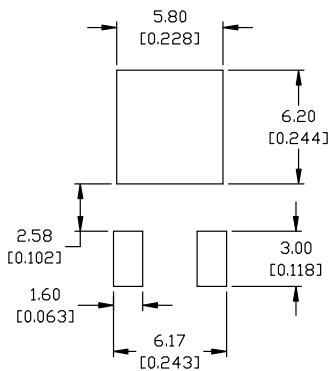
NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---



ALTERNATE CONSTRUCTIONS

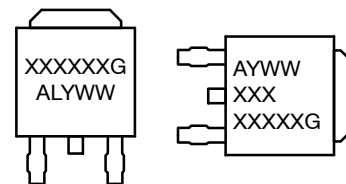


RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

- STYLE 1: PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 2: PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN
- STYLE 3: PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE
- STYLE 4: PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE
- STYLE 5: PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE
- STYLE 6: PIN 1. MT1
2. MT2
3. GATE
4. MT2
- STYLE 7: PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 8: PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE
- STYLE 9: PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE
- STYLE 10: PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

GENERIC MARKING DIAGRAM*



- IC Discrete
- XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)	PAGE 1 OF 1

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